

MEMC 98-3052 (2512.2)  
Patent

*4/29/02*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Robert J. Falster  
Serial No. TO BE ASSIGNED  
Filed January 3, 2002  
For SILICON ON INSULATOR STRUCTURE FROM LOW DEFECT DENSITY SINGLE  
CRYSTAL SILICON

January 3, 2002

PRELIMINARY AMENDMENT A

TO THE COMMISSIONER OF PATENTS AND TRADEMARKS,

SIR:

Please amend the application as follows:

In the Title:

Please change the title on page 1 to the following:

SILICON ON INSULATOR STRUCTURE HAVING A LOW DEFECT DENSITY  
DEVICE LAYER AND A PROCESS FOR THE PREPARATION THEREOF.

In the Specification:

Please replace the paragraph beginning on page 1, line 3  
with the following rewritten paragraph:

CROSS-REFERENCE TO RELATED APPLICATION

This application claims priority from U.S. provisional  
application Serial No. 60/098,902, filed on September 2, 1998,  
U.S. application Serial Number 09/387,288 filed on August 31,